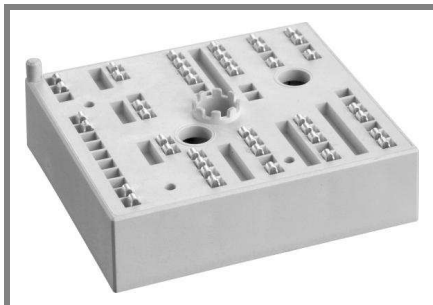


SKiiP 28GH066V1



MiniSKiiP[®]2

H-bridge inverter

SKiiP 28GH066V1

Features

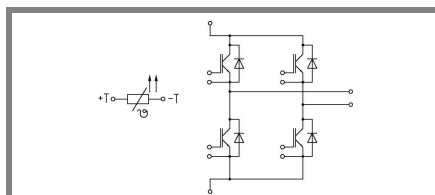
- Trench IGBTs
- Robust and soft freewheeling diode in CAL technology
- Highly reliable spring contacts for electrical connection
- UL recognised file no. E63532

Typical Applications*

- Single-phase inverter up to 16 kVA
- Single-phase motor power 7.5 kW

Remarks

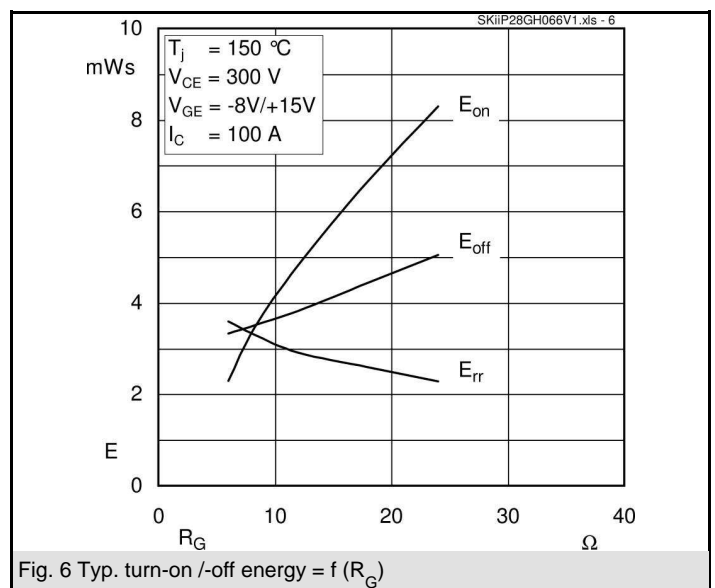
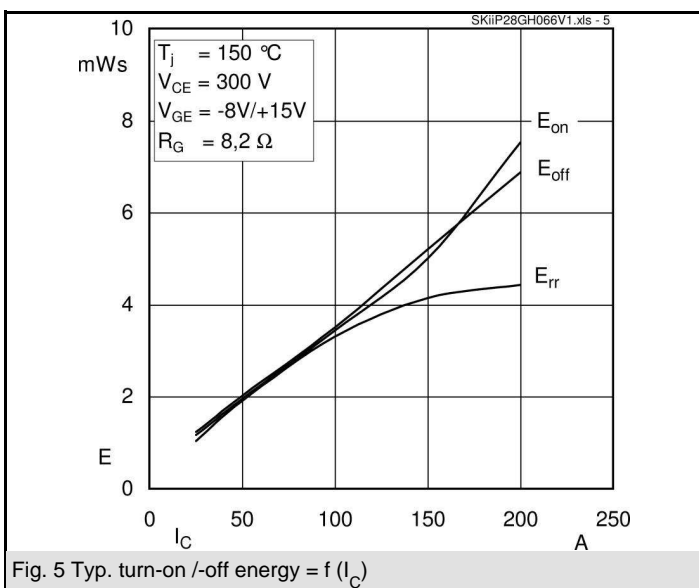
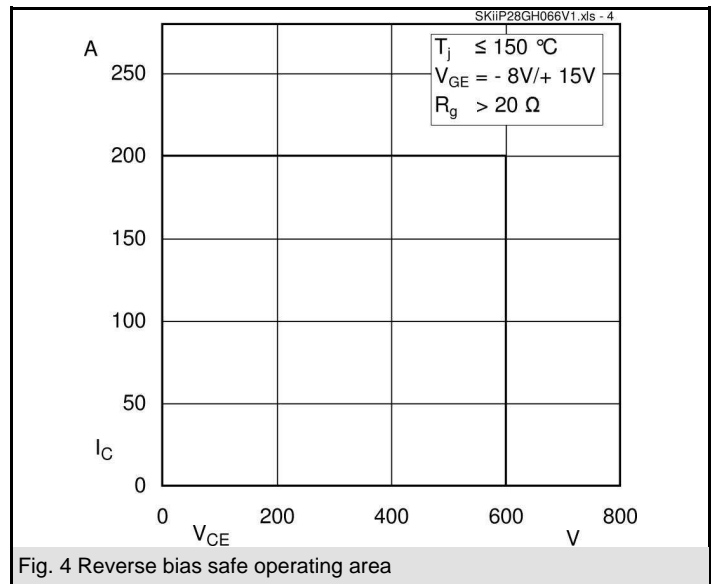
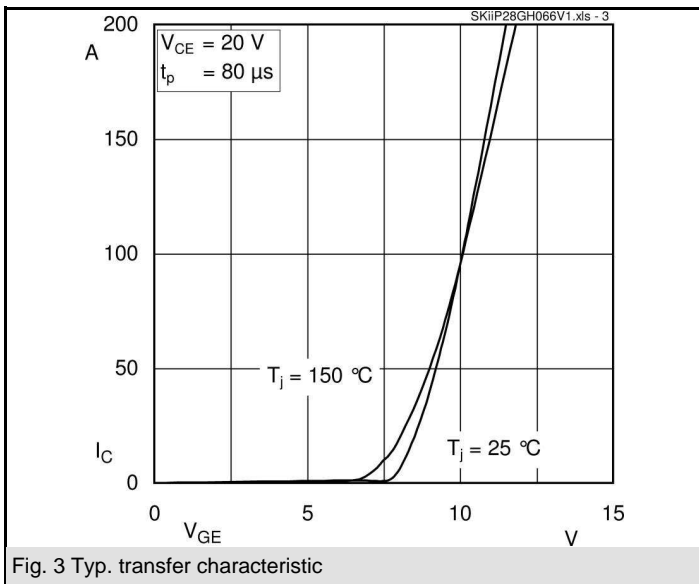
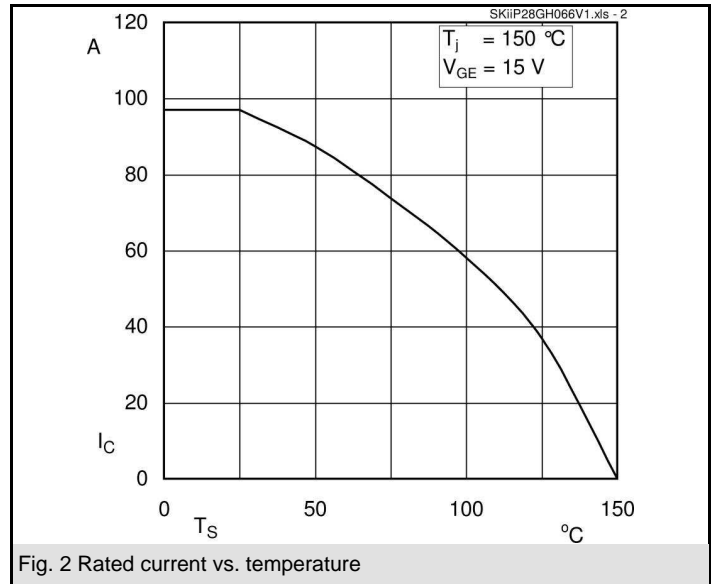
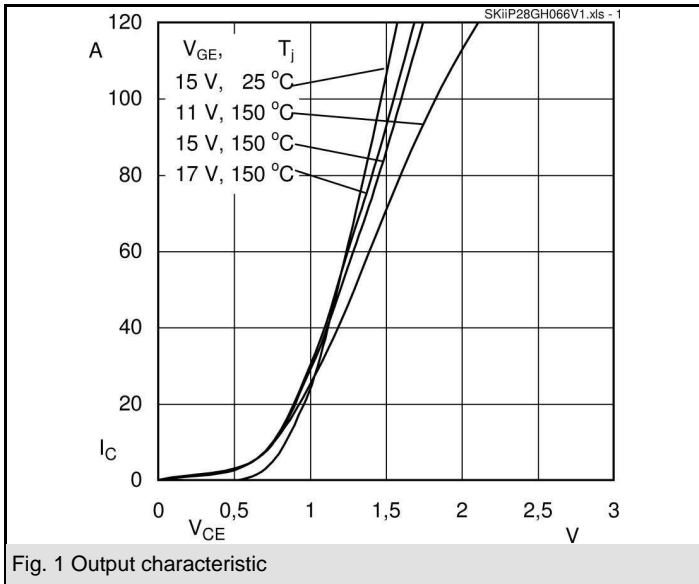
- Case temperature limited to $T_C = 125^\circ\text{C}$
- Product reliability results are valid for $T_j = 150^\circ\text{C}$
- SC data: $t_p \leq 6 \text{ s}$; $V_{GE} \leq 15 \text{ V}$; $T_j = 150^\circ\text{C}$, $V_{CC} = 360 \text{ V}$
- V_{CEsat} , $V_F =$ chip level value



GH

Absolute Maximum Ratings		$T_S = 25^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT - Inverter			
V_{CES}		600	V
I_C	$T_S = 25 (70)^\circ\text{C}, T_j = 150^\circ\text{C}$	101 (68)	A
I_C	$T_S = 25 (70)^\circ\text{C}, T_j = 175^\circ\text{C}$	112 (83)	A
I_{CRM}	$t_p = 1 \text{ ms}$	200	A
V_{GES}		± 20	V
T_j		-40...+175	$^\circ\text{C}$
Diode - Inverter			
I_F	$T_S = 25 (70)^\circ\text{C}, T_j = 150^\circ\text{C}$	103 (67)	A
I_F	$T_S = 25 (70)^\circ\text{C}, T_j = 175^\circ\text{C}$	112 (81)	A
I_{FRM}	$t_p = 1 \text{ ms}$	200	A
T_j		-40...+175	$^\circ\text{C}$
I_{RMS}	per power terminal (20 A / spring)	100	A
T_{stg}	$T_{op} \leq T_{stg}$	-40...+125	$^\circ\text{C}$
V_{isol}	AC, 1 min.	2500	V

Characteristics		$T_S = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter					
V_{CEsat}	$I_{Cnom} = 100 \text{ A}, T_j = 25 (150)^\circ\text{C}$	1,05	1,45 (1,65)	1,85 (2,05)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 2 \text{ mA}$		5,8		V
$V_{CE(TO)}$	$T_j = 25 (150)^\circ\text{C}$		0,9 (0,8)	1,1 (1)	V
r_T	$T_j = 25 (150)^\circ\text{C}$		5,5 (8,5)	7,5 (10,5)	m Ω
C_{ies}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		6,15		nF
C_{oes}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		1,12		nF
C_{res}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		0,9		nF
$R_{CC+EE'}$	spring contact-chip $T_S = 25 (150)^\circ\text{C}$				m Ω
$R_{th(j-s)}$	per IGBT		0,6		K/W
$t_{d(on)}$	under following conditions		40		ns
t_r	$V_{CC} = 300 \text{ V}, V_{GE} = -8\text{V}/+15\text{V}$		40		ns
$t_{d(off)}$	$I_{Cnom} = 100 \text{ A}, T_j = 150^\circ\text{C}$		410		ns
t_f	$R_{Gon} = R_{Goff} = 8,2 \Omega$		50		ns
$E_{on}(E_{off})$	inductive load		3,4 (3,5)		mJ
Diode - Inverter					
$V_F = V_{EC}$	$I_{Fnom} = 100 \text{ A}, T_j = 25 (150)^\circ\text{C}$		1,3 (1,3)	1,5 (1,5)	V
$V_{(TO)}$	$T_j = 25 (150)^\circ\text{C}$		0,9 (0,8)	1 (0,9)	V
r_T	$T_j = 25 (150)^\circ\text{C}$		4 (5)	5 (6)	m Ω
$R_{th(j-s)}$	per diode		0,8		K/W
I_{RRM}	under following conditions		102		A
Q_{rr}	$I_{Fnom} = 100 \text{ A}, V_R = 300 \text{ V}$		15,5		C
E_{rr}	$V_{GE} = 0 \text{ V}, T_j = 150^\circ\text{C}$		3,3		mJ
	$di_F/dt = 2560 \text{ A/ s}$				
Temperature Sensor					
R_{ts}	3 %, $T_r = 25 (100)^\circ\text{C}$		1000(1670)		Ω
Mechanical Data					
m			65		g
M_s	Mounting torque	2		2,5	Nm



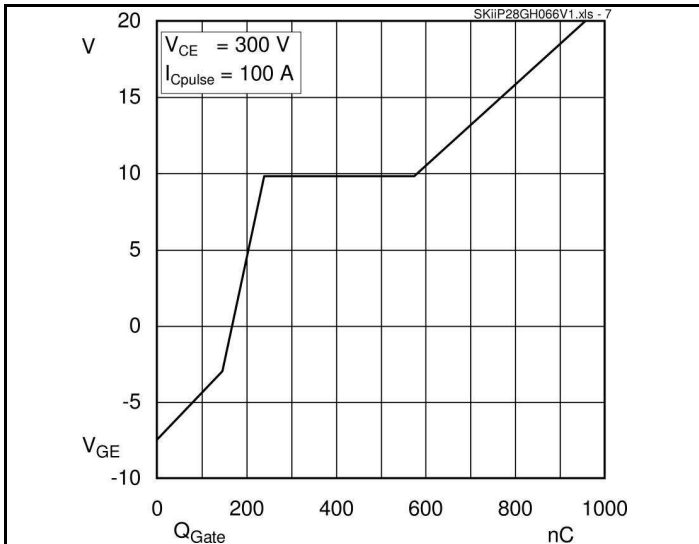


Fig. 7 Typ. Gate charge characteristic

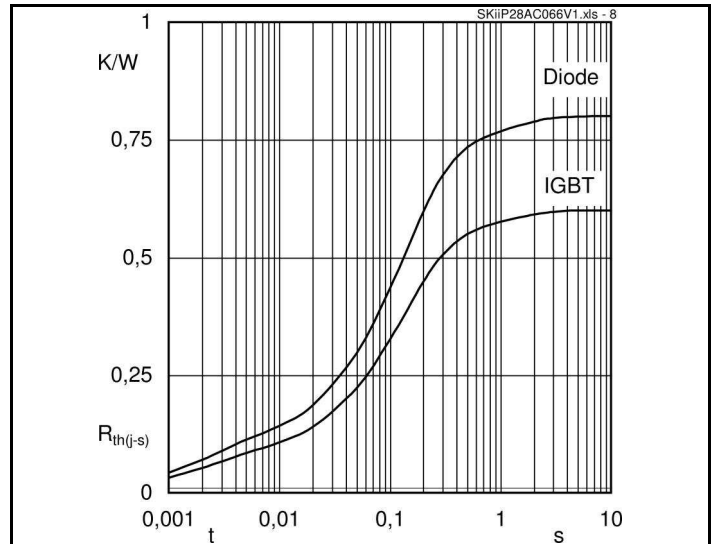


Fig. 8 Thermal impedance

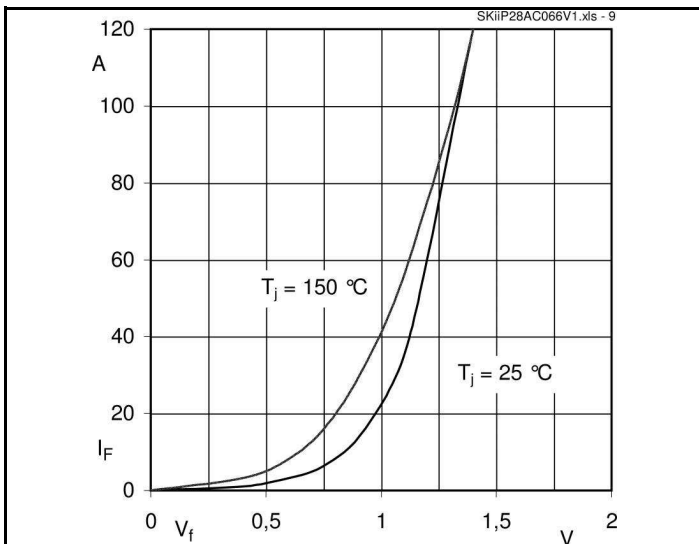
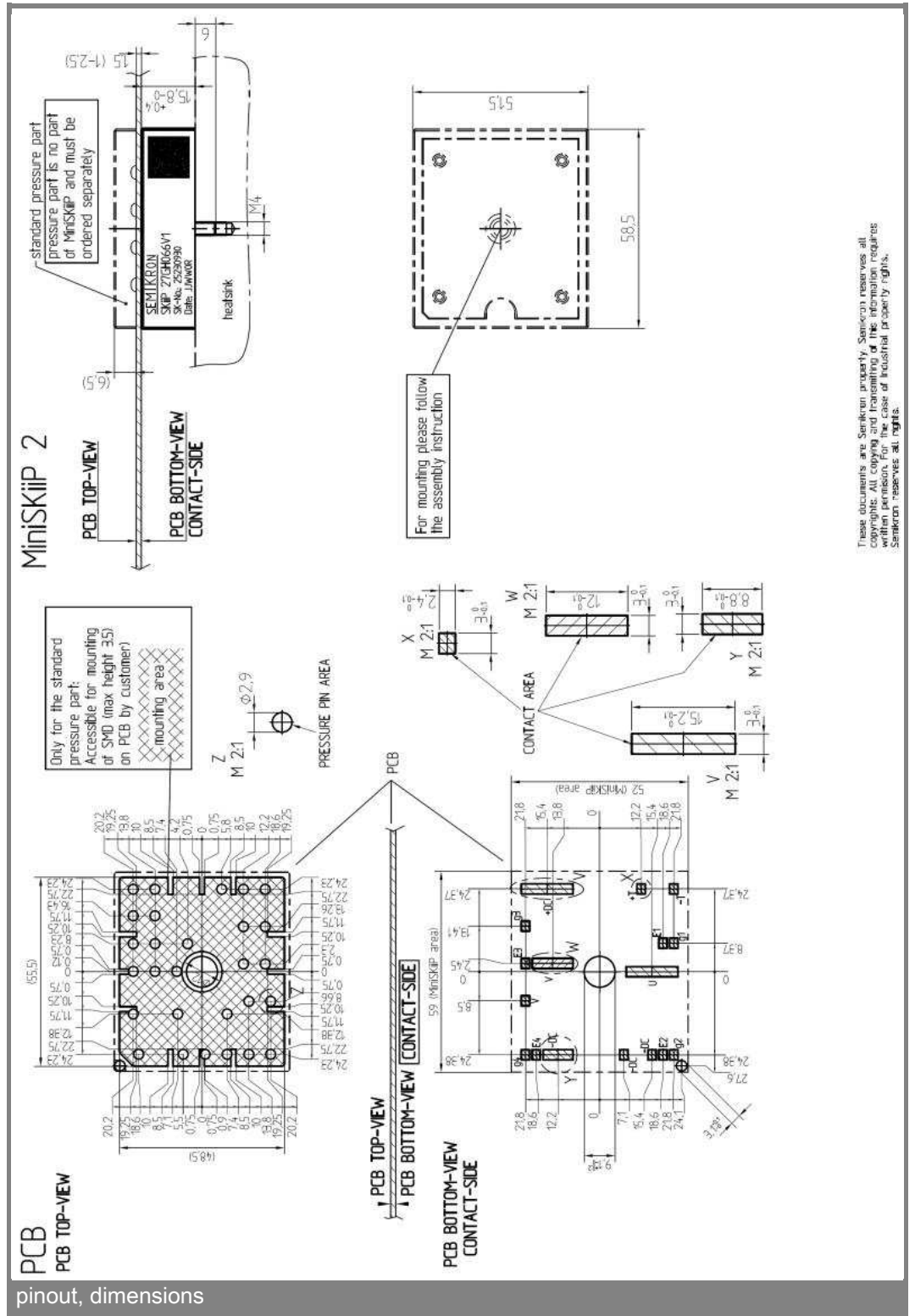
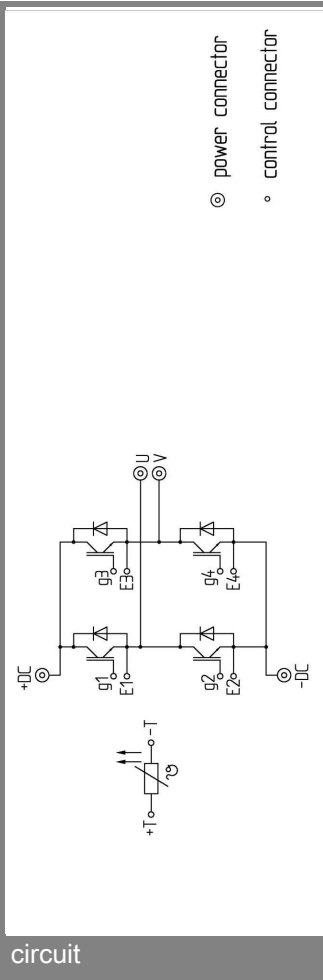


Fig. 9 Freewheeling diode forward characteristic



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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